

TRIAC series

1 Description

12A series triacs with low holding and latchingcurrent are especially recommended for use onmiddle and small resistance type power load.

(TO-220Alns) series provide insulation voltage rated at 2500V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906).

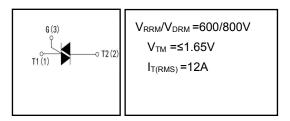
(TO-220F Ins) provides a rated insulation voltage of 2000VRMS, complying with UL standards (File ref: E252906).

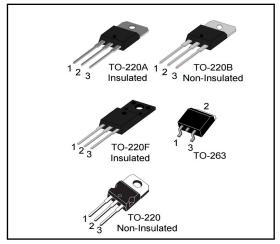
2 Features

- High current output up to 12A
- Low Peak on-state voltage drop
- High voltage
- High reliability

3 Applications

- jet pumps of dishwashers
- fans of air-conditioner
- power charger
- AC Motor control





4 Electrical Characteristics

4.1 Absolute Maximum Ratings (Tc=25 ℃, unless otherwise noted)

PARAMETER			SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (Tj=25℃)			V _{DRM}	600/800	V
Repetitive peak reverse voltage (Tj=25°C)			V_{RRM}	600/800	V
Non repetitive surge peak Off-state voltage	;		V _{DSM}	+ 100	V
Non repetitive peak reverse voltage			V_{RSM}	+ 100	V
TO-220(Ins)/TO-220F/ TO-263(T _C =85℃) TO-220(Non)/(T _C =110℃)		I _{T(RMS)}	12	A	
Non repetitive surge peak on-state current tp=8.3ms tp=10ms		tp=8.3ms	120		A
		tp=10ms	TTOW	110	
I ² t value for fusing (tp=10ms)	·		l ² t	72	Α
Repetitive rate of rise of on-state current (ITM=20A IG=50mA dIG/dt 50mA/ms)			d _{IT/dt}	50	A/us
Peak gate current			I _{GM}	2	Α
Peak gate power			P _{GM}	5	W
Average gate power dissipation			P _{G(AV)}	0.5	W
Operating junction temperature range			T_J	- 40 ~ 125	°C
Storage junction temperature range			T _{STG}	- 40 ~ 150	°C

4.2 Thermal Characteristics

PARAMETER	SYMBOL		UNIT		
FARAWETER	STIVIDOL	TO-220(Non)	To-220(Ins)	TO-220F/263	OINIT
Thermal Resistance, Junction to Case-sink	R _{thJC}	3.0	4.0	4.5	°C/W



4.3 Electrical Characteristics

(Tc=25℃,unless otherwise noted)

SYMBOL	PARAMETER	Test Condi	tions	Min	Тур	Max	Unit
			I - II -III	-	-	35	
I _{GT}	Triggering gate current	$V_D=12V R_L=33\Omega$	IV	-	-	-	mA
V _{GT}	Triggering gate voltage		ALL	-	-	1.5	V
V_{GD}	Non-triggering gate voltage	$V_D = V_{DRM} T_j = 125 ^{\circ} CR_L = 3.3 K\Omega$		0.2	-	-	V
			I -III	-	-	50	
I∟	Latching Current	I _G =1.2I _{GT}	II	-	-	60	mA
lΗ	Holding Current	I _T =100mA		-	-	40	mA
d _{V/dt}	Critical Rate of Rise of Off-state Voltage	V _D =2/3V _{DRM} Gate Op	en Tj=125℃	400	-	-	V/us
V _{TM}	Peak Forward On-State Voltage	I _{TM} =17A tp=380us		-	-	1.65	V
I _{DRM}			Tj=25°C	-	-	10	uA
	Maximum forward or reverse leakage current	$V_D=V_{DRM} V_R=V_{RRM}$					
I _{RRM}	Maximum reverse leakage current		Tj=125℃	-	-	1	mA

5 Typical characteristics diagrams

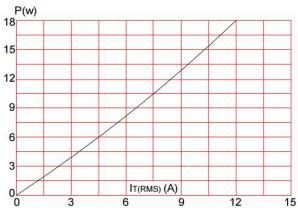


FIG.1: Maximum power dissipation versus RMS on-state current

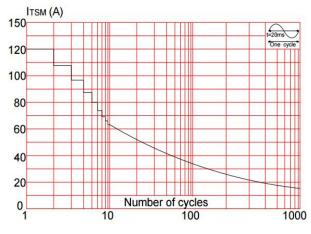


FIG.3: Surge peak on-state current versus number of cycles

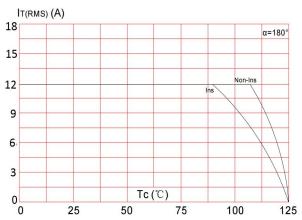


FIG.2: RMS on-state current versus case temperature

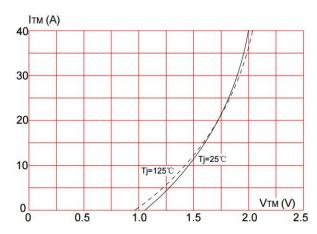


FIG.4: On-state characteristics (maximum values)



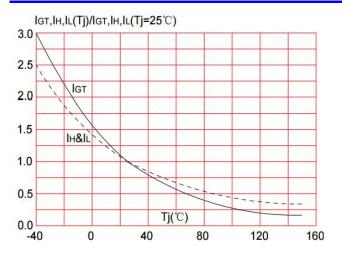
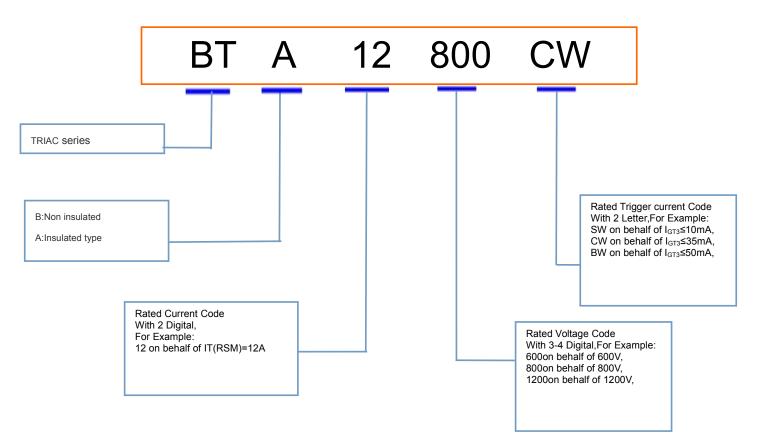


FIG.5: Relative variations of gate trigger current, holding current and latching current versus junction temperature

6 Product Names Rules

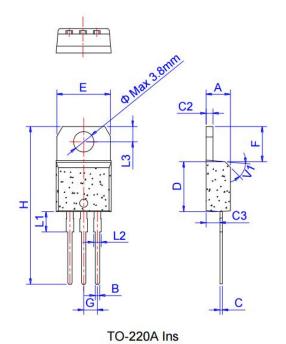


7 Product Specifications and Packaging Models

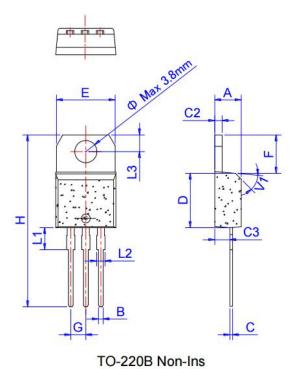
Produ	ıct Model	Package Type	Mark Name	RoHS	Package	Quantity
B	TA12	TO-220	BTA12	Pb-free	Tube	1000//box



8 Dimensions

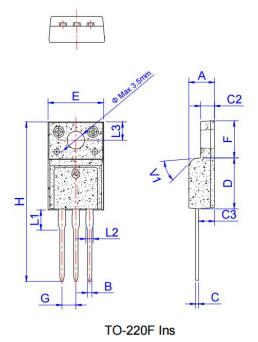


			Dime	ensions			
Ref.		Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.	
Α	4.40		4.60	0.173		0.181	
В	0.61		0.88	0.024		0.035	
С	0.46		0.70	0.018		0.028	
C2	1.21		1.32	0.048		0.052	
C3	2.40		2.72	0.094		0.107	
D	8.60		9.70	0.339		0.382	
Е	9.80		10.4	0.386		0.409	
F	6.55		6.95	0.258		0.274	
G		2.54			0.1		
Н	28.0		29.8	1.102		1.173	
L1		3.75			0.148		
L2	1.14		1.70	0.045		0.067	
L3	2.65		2.95	0.104		0.116	
V1		45°			45°	7,	



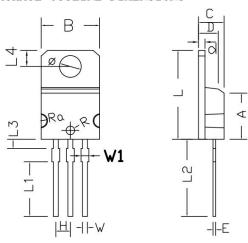
	Dimensions									
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С	0.46		0.70	0.018		0.028				
C2	1.21		1.32	0.048		0.052				
СЗ	2.40		2.72	0.094		0.107				
D	8.60		9.70	0.339		0.382				
E	9.60		10.4	0.378		0.409				
F	6.20		6.60	0.244		0.260				
G		2.54			0.1					
Н	28.0		29.8	1.102		1.173				
L1		3.75			0.148					
L2	1.14		1.70	0.045		0.067				
L3	2.65		2.95	0.104		0.116				
V1		45°			45°					





			Dime	ensions		
Ref.		Millimete	rs	Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.50		4.90	0.177		0.193
В	0.74	0.80	0.83	0.029	0.031	0.033
С	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
Н	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

TO-220M PACKAGE OUTLINE DIMENSIONS



Comb o 1	Dimensions	In Millimeters	Dimensions	In Inches
Symbol	min.	max.	min.	max.
	MIN	MAX	MIN	MAX
A	7. 55	8. 05	0. 297	0.317
В	9. 85	10. 25	0. 388	0. 404
C	4. 20	4. 80	0. 165	0. 189
D	3. 20	3. 60	0. 126	0. 142
Е	0.42	0. 47	0.017	0.019
L	15. 20	15. 60	0. 598	0.614
Н	2. 52	2. 56	0.099	0. 101
W	0.78	0.88	0.031	0. 035
Φ	3. 60	3.90	0. 142	0. 154
R	0.72	0.78	0.028	0. 031
Ra	9.00	10. 5	0. 354	0. 413
d	1. 10	1. 40	0.043	0.055
L1	9.3	9.7	0. 366	0. 382
L2	13.00	13.60	0. 512	0. 535
L3	1. 20	1.70	0. 047	0.067
L4	2.60	3. 0	0. 102	0.118
W1	1.10	1.50	0.043	0.059



9 Attentions

- Jiangsu Donghai Semiconductor Technology Co., Ltd. reserves the right to change the specification without prior notice! The customer should obtain the latest version of the information before making the order and verify that the information is complete and up to date.
- It is the responsibility of the purchaser for any failure or failure of any semiconductor product under certain conditions. It is the responsibility of the purchaser to comply with safety standards and to take safety measures in the system design and machine manufacturing of WXDH products in order to avoid potential risk of failure. Injury or property damage.
- Product promotion is endless, our company will be dedicated to provide customers with better products.

10 Appendix

Revision history:

Date	REV.	Description	Page
2017.09.8	1.0	Original	